	Application No.	Applicant(s)
Notice of Allowability	10/664,211	VERMA ET AL.
	Examiner	Art Unit
	Walter L. Lindsay, Jr.	2812
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGOT OF THE OFFICE OF UPON PETRON PROPRIED TO THE OFFICE OF UPON PETRON PROPRIED TO THE OFFICE OF THE OFFICE OFFICE OF THE OFFICE OF THE OFFICE OFFICE OFFICE OFFICE OF THE OFFICE O	OR REMAINS) CLOSED in this ap or other appropriate communicatio GHTS. This application is subject t	oplication. If not included n will be mailed in due course. THIS
1. \boxtimes This communication is responsive to <u>Election filed 9/16/200</u>	<u>94</u> .	
2. The allowed claim(s) is/are <u>1-16</u> .		
3. \boxtimes The drawings filed on <u>17 September 2003</u> are accepted by	the Examiner.	•
 4. Acknowledgment is made of a claim for foreign priority under a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: 	been received. been received in Application No	
Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONMI THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the requirements
5. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give		
 6. CORRECTED DRAWINGS (as "replacement sheets") must be submitted. (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date Identifying Indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d). 7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL. 		
 Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/06 Paper No./Mail Date 12/23/2003) 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	6. ☐ Interview Summary Paper No./Mail Da 8), 7. ☐ Examiner's Amend	ate

Application/Control Number: 10/664,211 Page 2

Art Unit: 2812

DETAILED ACTION

This Office action is in response to the Election requirement filed 9/16/2004.

Currently, claims 1-22 are pending. Claims 17-22 have been withdrawn.

Election/Restrictions

1. Applicant's election without traverse of claims 1-16 in the reply filed on 9/16/2004 is acknowledged.

- 2. Claims 17-22 have been withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a nonelected device, there being no allowable generic or linking claim. Election was made **without** traverse in the reply filed on 9/16/2004.
- 3. This application is in condition for allowance except for the presence of claims 17-22 to a device that is non-elected without traverse. Accordingly, claims 17-22 have been cancelled.

Allowable Subject Matter

- 4. Claims 1-16 are allowed.
- 5. The following is an examiner's statement of reasons for allowance: the prior art, either singly or in combination fails to anticipate or render obvious, the limitations of:
- planarizing said first dielectric layer and recessing said first dielectric layer below the level of said gate structure;

forming a second dielectric etch stop layer over said first dielectric layer;

planarizing said second dielectric layer in level with the gate structure;

pattern said second dielectric layer, using oversize gate mask to leave said second dielectric layer around said gate structure; and

forming electrical gate contact steps comprising: forming an inter-level dielectric layer over partially formed MOSFET device; patterning contact holes to source drain regions, patterning contact hole to gate stopping on said second dielectric layer; forming planarized metal patterns in and over said contact holes, as required by claim 1; and planarizing said silicon dioxide layer and recessing said silicon dioxide layer

planarizing said silicon dioxide layer and recessing said silicon dioxide layer below the level of said poly-silicon gate structure;

forming a silicon nitride etch stop layer over said silicon dioxide layer;

planarizing said silicon nitride etch stop layer, using oversize poly-silicon gate

mask to leave said silicon nitride layer around said poly-silicon gate structure; and

forming electrical poly-silicon gate contact steps comprising: forming an interlevel dielectric layer over partially formed MOSFET device; patterning contact holes to source drain regions, patterning contact hole to poly-silicon gate stopping on said silicon nitride etch stop layer; forming planarized metal patterns in and over said contact holes, as required by claim 11.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Walter L. Lindsay, Jr. whose telephone number is (571) 272-1674. The examiner can normally be reached on Monday-Thursday.

Application/Control Number: 10/664,211 Page 4

Art Unit: 2812

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John F Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

November 2, 2004

/ John F. Niabling
Supervisory Patent Exeminer
Technology Center 2890